



Band switching diode

Features

1. Low differential forward resistance
2. Low diode capacitance
3. High reverse impedance
4. Micro Melf package, fits onto SOD-323/SOT-23 footprints



Applications

Band switching in VHF-tuners

Absolute Maximum Ratings

$T_J=25\text{ }^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
DC Reverse voltage		V_R	35	V
Power dissipation		P_d	150	MW
Junction temperature		T_J	125	$^{\circ}\text{C}$
Operation temperature range		T_{opr}	-20 ~ +60	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-45 ~ +125	$^{\circ}\text{C}$

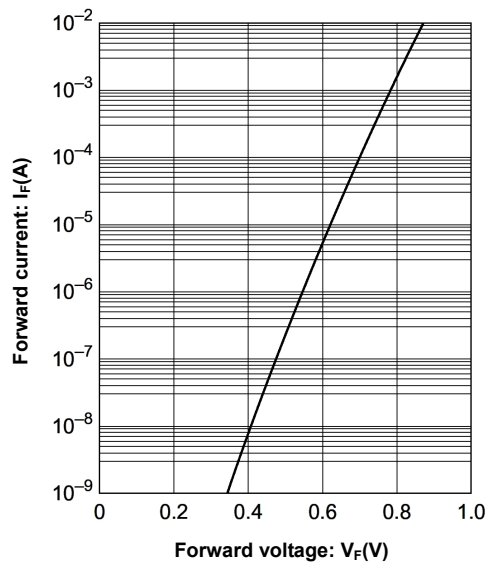
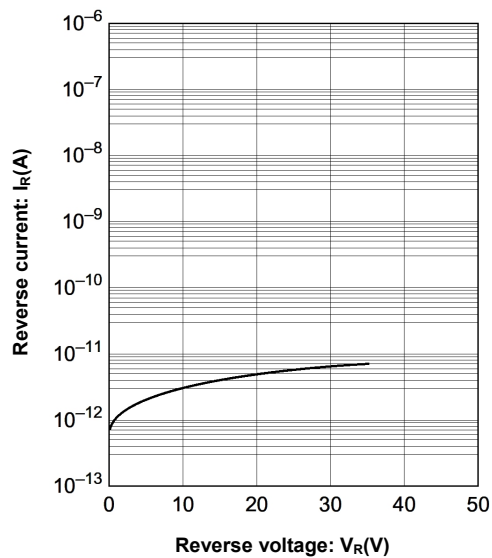
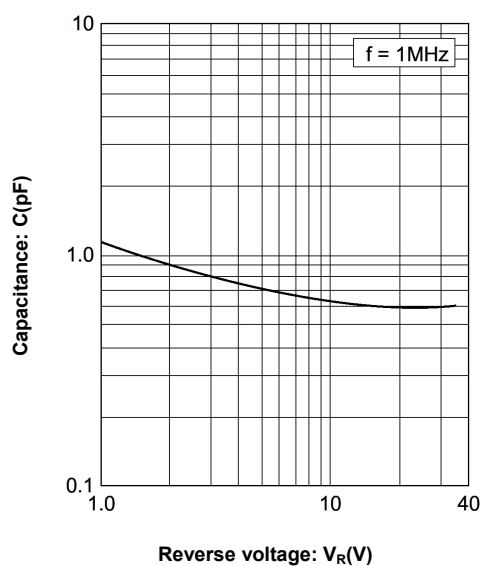
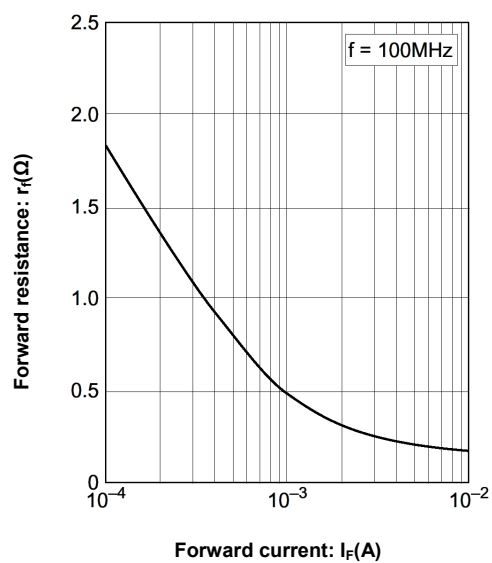
Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

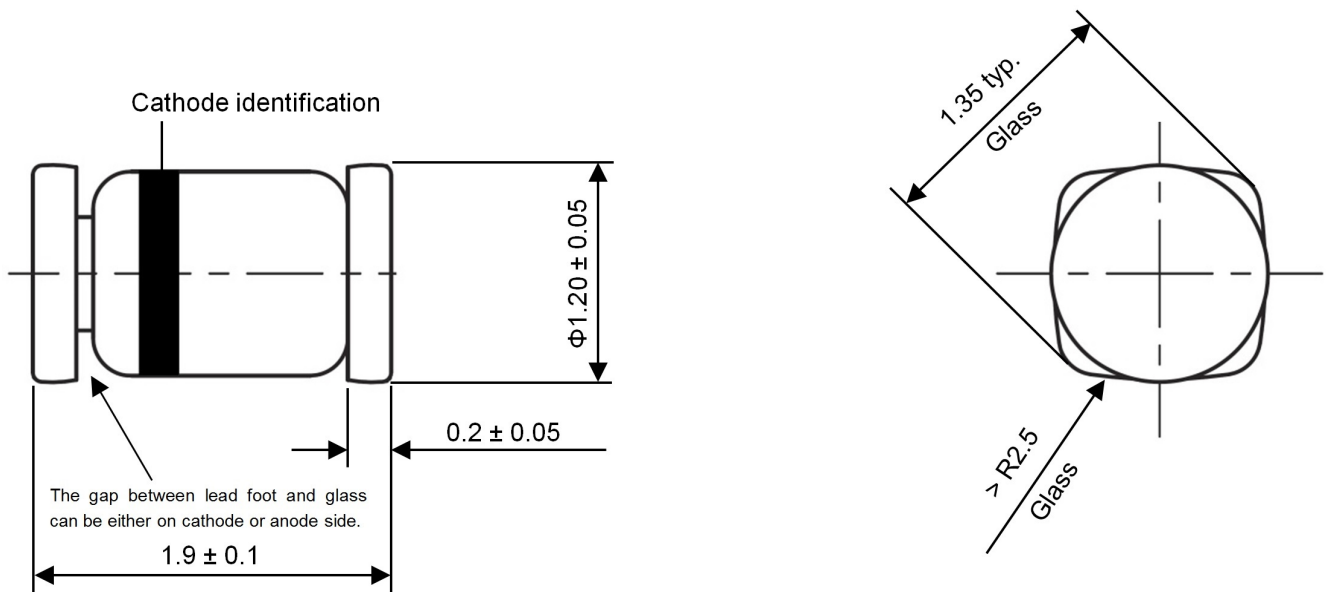
Electrical Characteristics

$T_J=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=10\text{mA}$	V_F			1	V
Reverse current	$V_R=25\text{V}$	I_R			50	nA
Reverse voltage	$I_R=10\mu\text{A}$	B_V	35			V
Capacitance	$f=1\text{MHz}$, $V_R=6\text{V}$	C_t			1.2	pF
Forward resistance	$f=100\text{MHz}$, $I_F=2\text{mA}$	r_f			0.7	Ω

Excel Semiconductor

**Characteristics ($T_j=25$** **$^{\circ}\text{C}$ unless otherwise specified)****Figure 1. Forward current vs. forward voltage****Figure 2. Reverse current vs. reverse voltage****Figure 3. Capacitance vs. reverse voltage****Figure 4. Forward resistance vs. forward current**

**Dimensions in mm**

Glass Case
Micro Melf